

AMENDMENTS TO THE CLAIMS

Please amend Claims 34 and 36 as follows. The following listing of claims will replace all prior versions and listings of claims in the application.

LISTING OF CLAIMS

1. (previously presented) A method of etching a metallic film, comprising the steps of:

forming a metallic film on a thin film resistor;

forming a conductive film on the metallic film;

forming a first opening in the conductive film to expose the metallic film from the first opening;

forming a mask on the conductive film after forming the first opening, the mask having a second opening having an opening area smaller than that of the first opening and open in the first opening to expose the metallic film therefrom; and

etching the metallic film through the second opening.

2. (original) The method of Claim 1, wherein the step of etching the metallic film includes steps of:

dry-etching a first part of the metallic film through the second opening; and

wet-etching a second part of the metallic film, the second part directly contacting the thin film resistor.

3. (original) The method of Claim 1, wherein a side wall of the first opening is entirely covered with the mask defining the second opening therein.

4. (previously presented) The method of Claim 1, wherein the step of forming the mask includes steps of:

forming a photo-resist on the conductive film and in the first opening to serve as the mask; and

removing a part of the photo-resist to form the second opening.

5-6. (cancelled)

7. (previously presented) The method of Claim 2, wherein a thickness of the first part is equal to or larger than 20% relative to an entire thickness of the metallic film.

8. (previously presented) The method of Claim 2, wherein a thickness of the second part is equal to or larger than 100 Å.

9. (previously presented) The method of Claim 2, wherein the step of dry-etching the metallic film uses an etching gas including CF_4 .

10. (previously presented) The method of Claim 2, wherein the step of wet-etching the metallic film uses an etching solution including H_2O_2 .

11. (previously presented) The method of Claim 2, wherein the metallic film is formed with a thickness equal to or larger than 500 Å.

12-25. (cancelled)

26. (previously presented) The method of Claim 2, wherein the metallic film is a single layer.

27. (previously presented) The method of Claim 2, wherein the metallic film is directly disposed on the thin film resistor.

28-32. (cancelled)

33. (previously presented) The method of Claim 1, wherein the mask is formed to cover a sidewall of the conductive film defining the first opening.

34. (currently amended) A method of etching a metallic film, comprising:
forming a metallic film;
forming a conductive film on the metallic film, the conductive film being different substance from the metallic film;
forming an opening in the conductive film to expose a sidewall of the conductive film and a portion of the underlying metallic film through the opening;

forming a masking film over the conductive film after forming the opening, the masking film having a pattern which exposes a part of the portion of the metallic film in the opening ~~with the sidewall of the conductive film covered~~ and covers the sidewall of the conductive film in the opening; and

etching the metallic film using the masking film as an etching mask, the etching including wet etching;

~~wherein a length of the masking film covering the metallic film in the opening is controlled in association with a side etching amount of the metallic film during the etching.~~

35. (previously presented) The method of Claim 34, wherein an ionization tendency of the conductive film is larger than that of the metallic film.

36. (currently amended) The method of Claim 34, further comprising, prior to the forming the metallic film, forming a resistive film, the ~~conductive~~ metallic film being formed on the resistive film.

37. (previously presented) The method of Claim 36, wherein the ionization tendency of the metallic film is larger than that of the resistive film.

38. (previously presented) The method of Claim 37, wherein an ionization tendency of the conductive film is larger than that of the metallic film.

39-40. (cancelled)

41. (previously presented) The method of Claim 34, wherein the etching includes dry etching prior to the wet etching.

42. (cancelled)